



#26/DS
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R. St. John

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT APPLICATION

In re application of

Akitaka KIMURA

Appln. No.: 09/161,981

Confirmation No.: 8269

Filed: September 29, 1998

Docket No: Q51885

Group Art Unit: 2812

Examiner: J. Davie

For: SEMICONDUCTOR LAYER FORMED BY SELECTIVE DEPOSITION AND
METHOD FOR DEPOSITING SEMICONDUCTOR LAYER

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. §§ 1.97 and 1.98

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

1. S. Nakamura et al., Ridge-geometry InGa_N multi-quantum-well-structure laser diodes, Appl. Phys. Lett., 69(1996) 1577.
2. S. Nakamura et al., Bluish-Pruple InGa_N Multi-Quantum Well Structure Laser Diodes, Extended Abstracts of 1996 International Conference on Solid State Devices and Materials, Yokohama, 1996, pp.67-69)

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INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: 09/161,981

3. Japanese Unexamined Patent Publication No. H08-018159, published January 19, 1996.
4. Japanese Unexamined Patent Publication No. H04-340284, published November 26, 1992.
5. Japanese Unexamined Patent Publication No. H09-036473, published February 7, 1997.
6. Japanese Unexamined Patent Publication No. H08-264454, published October 11, 1996.
7. Japanese Unexamined Patent Publication No. H09-036475, published February 7, 1997.
8. Japanese Unexamined Patent Publication No. H09-199791, published July 31, 1997.
9. Isamu Akasaki III-V-Family Compound Semiconductors: Baifukan, 1994, page 335

One copy of each of the listed documents is submitted herewith.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date for an application other than a continued prosecution application (CPA) under §1.53(d); (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

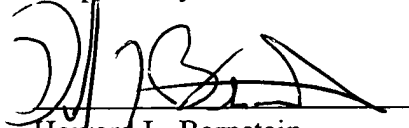
INFORMATION DISCLOSURE STATEMENT
U.S. Appln. No.: 09/161,981

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant states that above-identified references 1 and 2 are discussed within the specification beginning at page 3, line 24, and page 2, line 21, respectively.

Also in compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant encloses here with a copy of a corresponding Japanese Office Action and an English translation of the pertinent portions thereof which cites documents 3-8 and indicates the degree of relevance found by the foreign office. Additionally, Applicant encloses a copy of a subsequently issued Japanese Office Action and an English translation of the pertinent portions thereof which cites document 9 and indicates the degree of relevance found by the foreign office.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

Respectfully submitted,


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WASHINGTON OFFICE



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PATENT TRADEMARK OFFICE

Date: June 11, 2003

Substitute for Form 1449 A & B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet

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of

1

Complete if Known

Application Number	09/161,981
Confirmation Number	8269
Filing Date	September 29, 1998
First Named Inventor	Akitaka KIMURA
Art Unit	2812
Examiner Name	J. Davie
Attorney Docket Number	Q51885

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
		US			
		US			
		US			
		US			
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
		JP	H08-18159		01-19-1996		No
		JP	H04-340284		11-26-1992		No
		JP	H09-036473		02-07-1997		No
		JP	H08-264454		10-11-1996		No
		JP	H09-036475		02-07-1997		No
		JP	H09-199791		07-31-1997		No

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation
		Nakamura et al., Ridge-geometry InGa _N multi-quantum-well-structure laser diodes, Appl. Phys. Lett., 69(1996) 1577.	
		S. Nakamura et al., Bluish-Pruple InGa _N Multi-Quantum Well Structure Laser Diodes, Extended Abstracts of 1996 International Conference on Solid State Devices and Materials, Yokohama, 1996, pp.67-69	
		Isamu Akasaki III-V-Family Compound Semiconductors: Baifukan, 1994, page 335	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to indicate here if English language Translation is attached.